

Silicon Power Schottky Diode

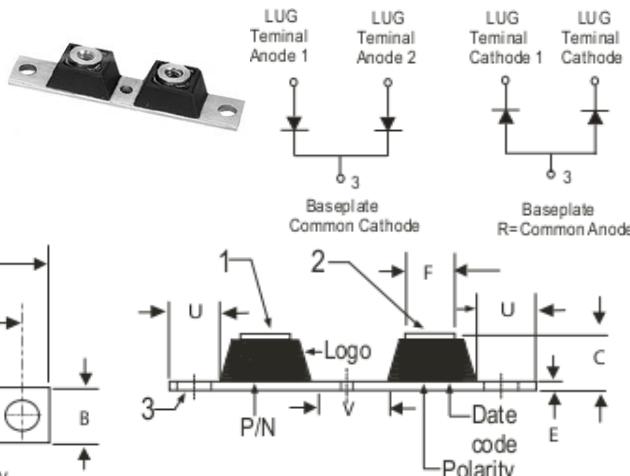
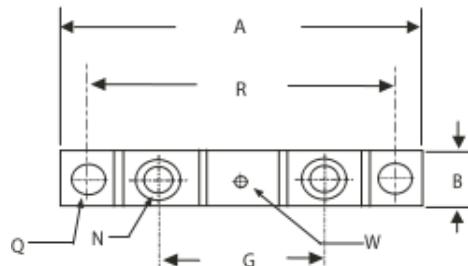
Twin Tower Package

 $V_{RRM} = 20 \text{ V - } 100 \text{ V}$
 $I_F = 500 \text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}

TWIN TOWER



Maximum ratings, at $T_j = 25 \text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR50045CT (R)	MBR50060CT (R)	MBR50080CT (R)	MBR500100CT (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		45	60	80	100	V
RMS reverse voltage	V_{RMS}		32	42	56	70	V
DC blocking voltage	V_{DC}		45	60	80	100	V
Continuous forward current	I_F	$T_C \leq 100 \text{ }^\circ\text{C}$	500	500	500	500	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25 \text{ }^\circ\text{C}, t_p = 8.3 \text{ ms}$	3500	3500	3500	3500	A
Operating temperature	T_j		-40 to 150	-40 to 150	-40 to 150	-40 to 150	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25 \text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBR50045CT (R)	MBR50060CT (R)	MBR50080CT (R)	MBR500100CT (R)	Unit
Diode forward voltage	V_F	$I_F = 250 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	0.75	0.8	0.88	0.88	V
Reverse current	I_R	$V_R = 20 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$	1	1	1	1	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.12	0.12	0.12	0.12	$^\circ\text{C/W}$
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